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SOT-89 PNP Silicon PNP transistor in a SOT-89 Plastic Package.

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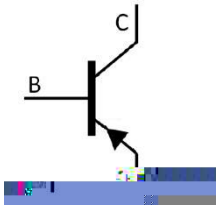
, 2SD1766

Low $V_{CE(sat)}$,complements the 2SD1766.

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Medium power amplifier applications.

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PIN1 Base PIN 2 Collector PIN 3 Emitter

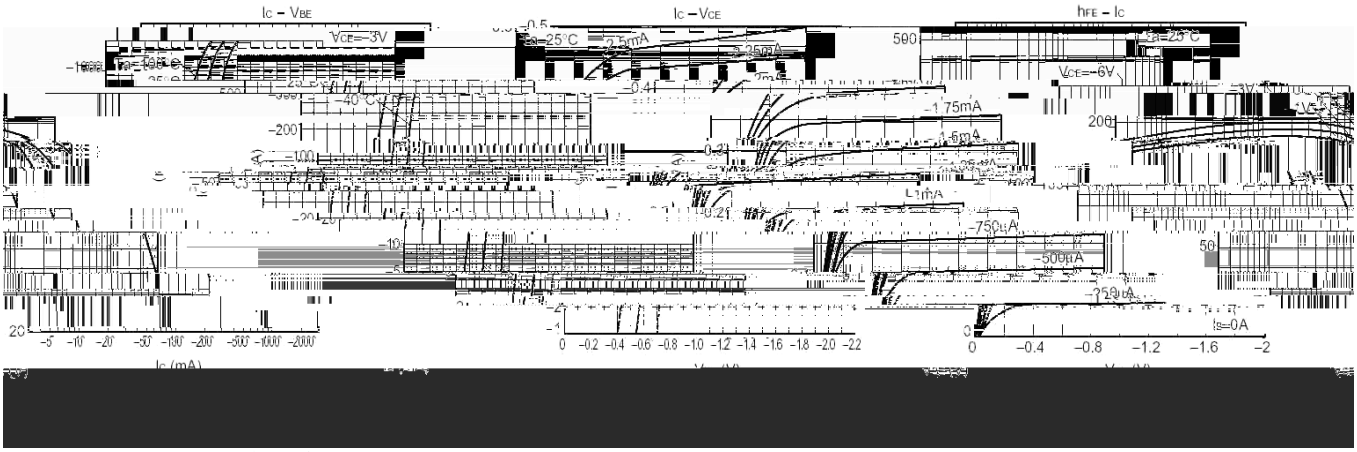
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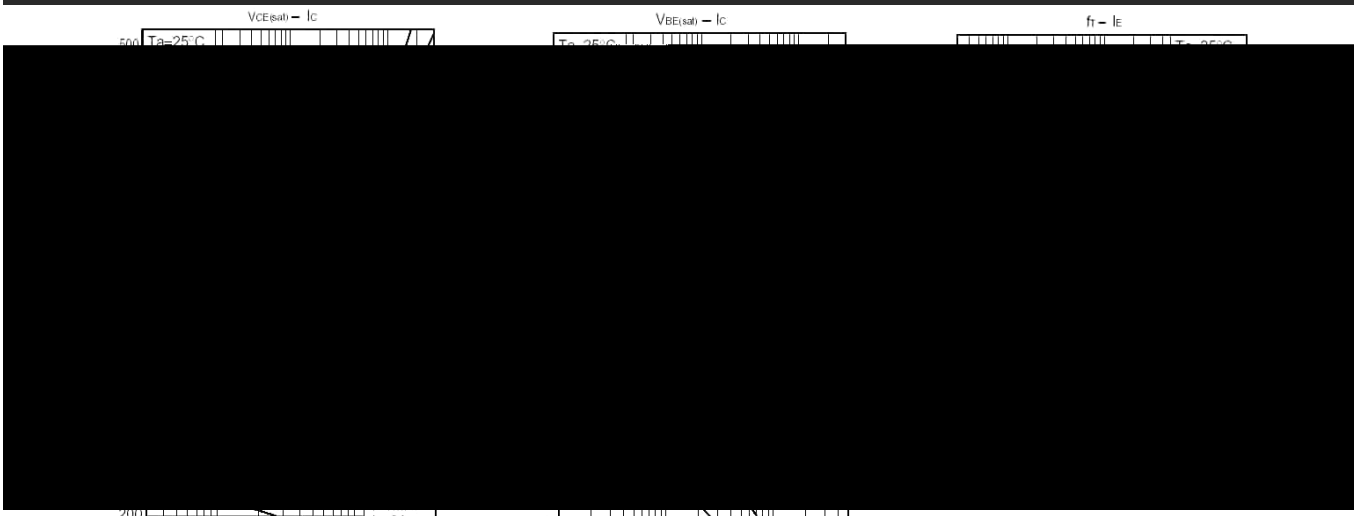
h_{FE} Classifications Symbol	P	Q	R
h_{FE} Range	82 180	120 270	180 390
Marking	HBCP	HBCQ	HBCR

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V

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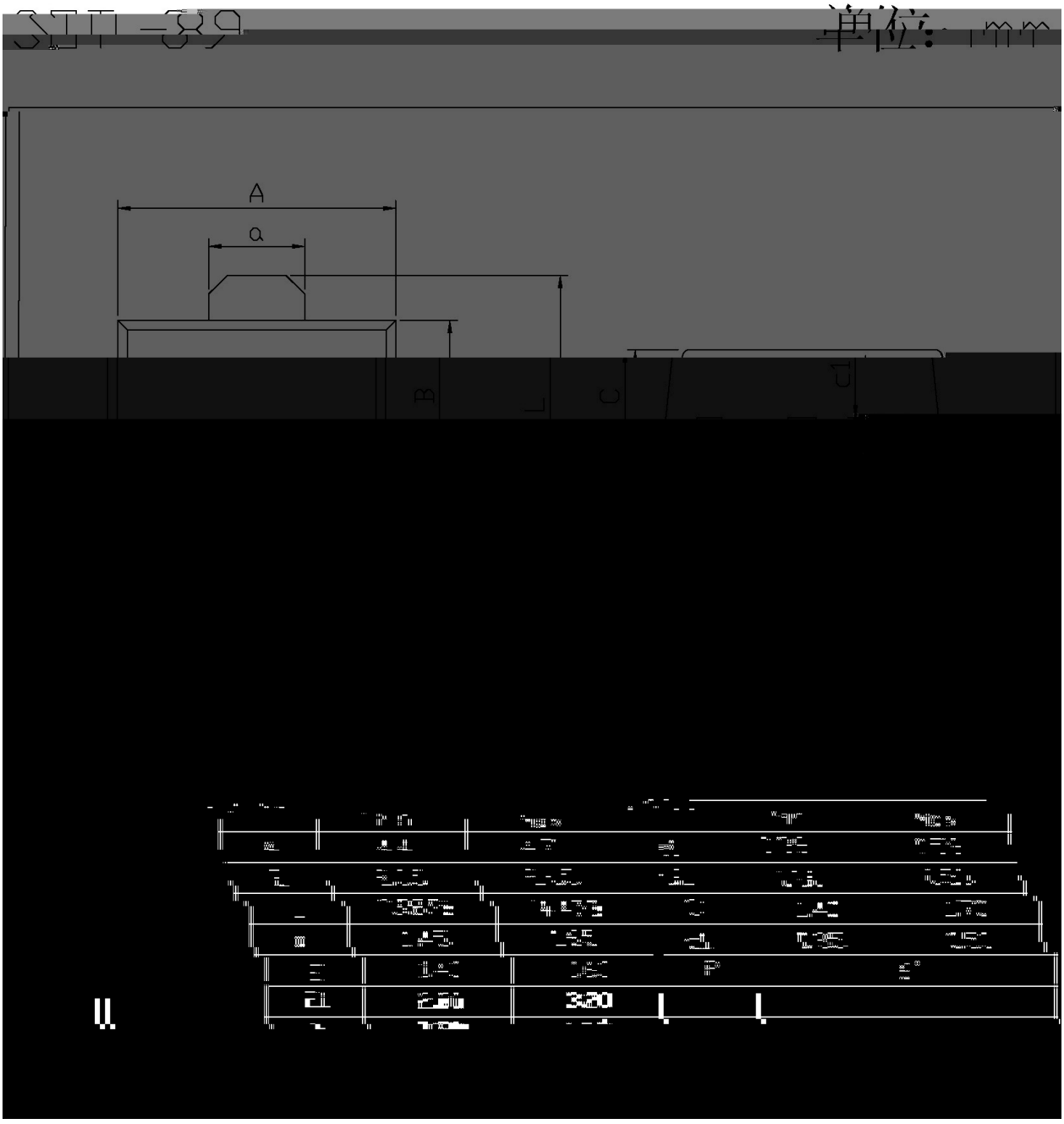
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IC – VBE
VCE=–3V
Ta=25°C
IC – VCE
Ta=25°C
hFE – IC
Ta=25°C
VCE=–6V
–1.75mA
–1.5mA
–1.25mA
–1mA
–750μA
–500μA
–250μA
IB=0A
IC (mA)

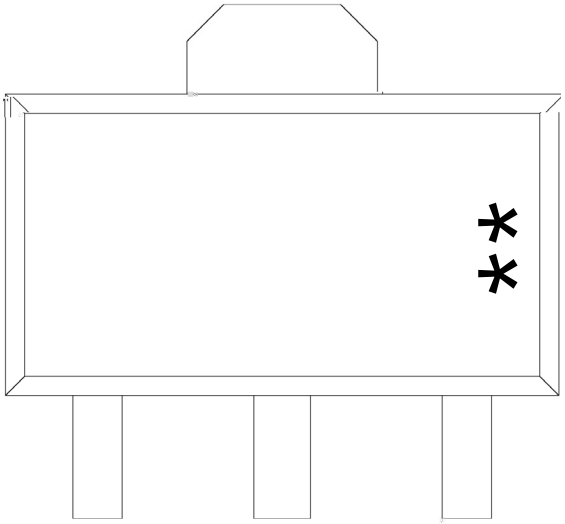

VCE(sat) – IC
Ta=25°C
VBE(sat) – IC
fT – IE


IE=0A
IC=0A
100ms
10ms
1ms
PW
DC
Cob
200
100
50
20

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H

BC

P h_{FE}

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Note:

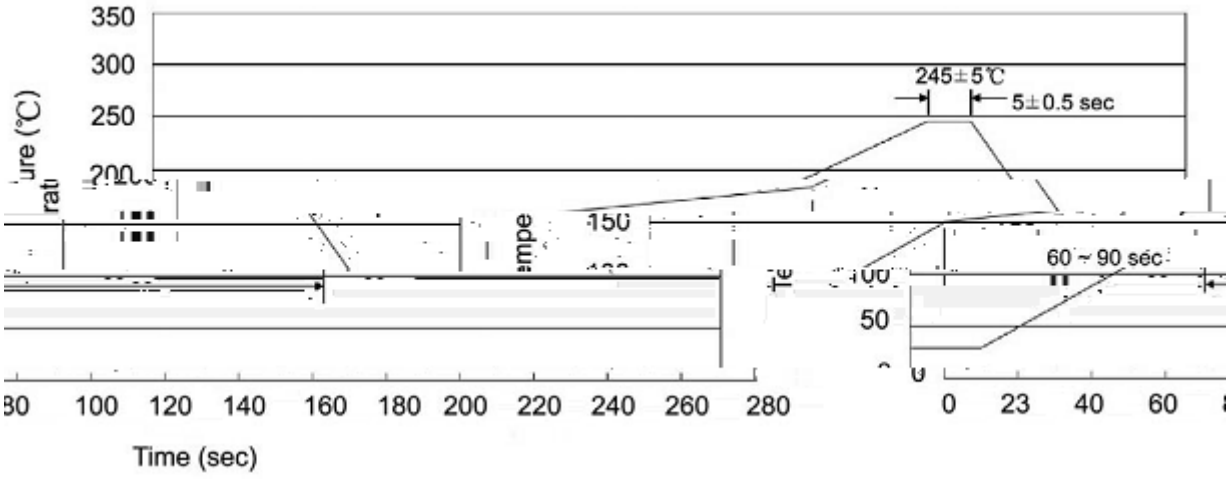
H: Company Code.

BC: Product Type.

P h_{FE} Classifications Symbol

**: Lot No. Code, code change with Lot No.

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Note:

1 25 150 60 90sec;

1.Preheating:25~150 , Time:60~90sec.

2 245±5 5±0.5sec;

2.Peak Temp.:245±5 , Duration:5±0.5sec.

3 2 10 /sec.

3. Cooling Speed: 2~10 /sec.

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260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

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/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-89	1,000	7	7,000	8	56,000	7 ×12	180×120×180	385×257×392

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